

5. (Amended) A field emitter display device, comprising:

at least one emitter having an implantation [that emits] for emitting electrons at a predetermined energy level, wherein the implantation [affects the lowering mechanism so as] is conforming to a surface of the at least one emitter for affecting a lowering mechanism to enhance the emission of electrons.

7. (Amended) A field emitter display device, comprising:

at least one emitter having an implantation [that releases] for releasing electrons at a predetermined energy level, wherein the implantation [affects the image force so as] is conforming to a surface of the at least one emitter for affecting an image force to enhance the releasing of electrons.

9. (Amended) A field emitter display device, comprising:

at least one emitter having an implantation [that emits] for emitting electrons at a predetermined energy level, wherein the implantation [enhances] is conforming to a surface of the at least one emitter for enhancing the Schottky effect [so as] to enhance the emission of electrons.

11. (Amended) A field emitter display device, comprising:

at least one emitter having an implantation [that releases] for releasing electrons at a predetermined energy level, wherein the implantation [decreases the] is conforming to a surface of the at least one emitter for decreasing a dielectric effect of the at least one emitter to enhance the releasing of electrons.

13. (Amended) A field emitter display device, comprising:

at least one emitter having an ion implantation layer [that releases] for releasing electrons at a predetermined energy level, wherein the ion implantation layer [enhances] is conforming to a surface of the at least one emitter for enhancing the releasing of electrons and [the layer limits the] for limiting an outgassing [so as] to inhibit degradation of the at least one emitter.

15. (Amended) A field emitter display device, comprising:

at least one emitter having an implantation layer [that releases] for releasing electrons at a predetermined energy level, wherein the implantation layer [lowers the] is conforming to a surface of the at least one emitter for lowering a potential barrier to enhance the releasing of electrons and [the layer limits the] for limiting an outgassing [so as] to inhibit degradation of the at least one emitter.

17. (Amended) A field emitter display device, comprising:

at least one emitter having an implantation layer [that releases] for releasing electrons at a predetermined energy level, wherein the implantation layer [affects the] is conforming to a surface of the at least one emitter for affecting an image force [so as] to enhance the releasing of electrons and [the implantation layer limits the] for limiting an outgassing [so as] to inhibit degradation of the at least one emitter.

19. (Amended) A field emitter display device, comprising:

at least one emitter having an implantation layer [that emits] for emitting electrons at a predetermined energy level, wherein the implantation layer [improves] is conforming to a surface of the at least one emitter for improving the Schottky effect [so as] to enhance the emission of electrons and [the implantation layer limits the] for limiting an outgassing [so as] to inhibit degradation of the at least one emitter.

21. (Amended) A field emitter display device, comprising:

at least one emitter having an implantation layer [that releases] for releasing electrons at a predetermined energy level, wherein the implantation layer [decreases the] is conforming to a surface of the at least one emitter for decreasing a dielectric effect of the at least one emitter to enhance the releasing of electrons and [the implantation layer limits the] for limiting an outgassing [so as] to inhibit degradation of the at least one emitter.

23. (Amended) A field emitter display device, comprising:

at least one emitter having a silicon oxide ion implantation layer conforming to a surface of the at least one emitter.

24. (Amended) A field emitter display device, comprising:

at least one emitter having an oxide implantation layer [that releases] conforming to a surface of the at least one emitter for releasing electrons at a predetermined energy level.

25. (Amended) A field emitter display device, comprising:

at least one emitter having an embedded silicon oxide layer conforming to a surface of the at least one emitter.

27. (Amended) A field emitter display device, comprising:

at least one emitter having an external coating and an embedded layer [that releases] for releasing electrons at a predetermined energy level, wherein the embedded layer [limits] is conforming to a surface of the at least one emitter for limiting an outgassing to inhibit degradation of the at least one emitter and [enhances] for enhancing the releasing of electrons.

28. (Amended) A field emitter display device, comprising:

at least one emitter having an external coating and an embedded layer [that releases] for releasing electrons at a predetermined energy level, wherein the embedded layer [limits] is conforming to a surface of the at least one emitter for limiting an outgassing to inhibit degradation of the at least one emitter and [lowers the] for lowering a potential barrier to enhance the releasing of electrons.

29. (Amended) A field emitter display device, comprising:

at least one emitter having an external coating and an embedded layer [that releases] for releasing electrons at a predetermined energy level, wherein the embedded layer [limits] is conforming to a surface of the at least one emitter for limiting an outgassing to inhibit degradation of the at least one emitter and [affects the] for affecting a lowering mechanism [so as] to enhance [the] an emission of electrons.

30. (Amended) A field emitter display device, comprising:

at least one emitter having an external coating and an embedded layer [that releases] for releasing electrons at a predetermined energy level, wherein the embedded layer [limits] is conforming to a surface of the at least one emitter for limiting an outgassing to inhibit degradation of the at least one emitter and [affects the] for affecting an image force [so as] to enhance the releasing of electrons.

31. (Amended) A field emitter display device, comprising:

at least one emitter having an external coating and an embedded layer [that releases] for releasing electrons at a predetermined energy level, wherein the embedded layer [limits] is conforming to a surface of the at least one emitter for limiting an outgassing to inhibit degradation of the at least one emitter and [improves] for improving the Schottky effect [so as] to enhance [the] an emission of electrons.

32. (Amended) A field emitter display device, comprising:

at least one emitter having an external coating and an embedded layer [that releases] for releasing electrons at a predetermined energy level, wherein the embedded layer [limits] is conforming to a surface of the at least one emitter for limiting an outgassing to inhibit degradation of the at least one emitter and [decreases the] for decreasing a dielectric effect of the at least one emitter to enhance the releasing of electrons.

33. (Amended) A field emitter display device, comprising:

at least one emitter having an implantation [that releases] for releasing electrons at a predetermined energy level, wherein the implantation [reduces the] is conforming to a surface of the at least one emitter for reducing a potential barrier to enhance the releasing of electrons and [inhibits] for inhibiting degradation of the at least one emitter in the presence of the outgassing; and

a light-emitting target [that radiates] for radiating [when the released electrons strike the light-emitting target] in response to the released electrons.